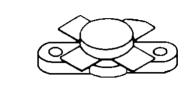


SD1224-10

RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

- 30 MHz
- 28 VOLTS
- IMD -28 dB
- **COMMON EMITTER**
- GOLD METALLIZATION
- P_{OUT} = 30 W MIN. WITH 18 dB GAIN



.380 4LFL (M113)

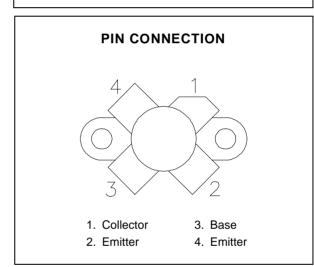
epoxy sealed

ORDER CODE SD1224-10 BRANDING

1224-10

DESCRIPTION

The SD1224-10 is a 28 V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes emitter ballasting for improved ruggedness and reliability.



ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	65	V	
VCEO	Collector-Emitter Voltage	36	V	
V _{EBO}	Emitter-Base Voltage	4.0	V	
Ic	Device Current	4.5	А	
P _{DISS}	Power Dissipation	80	W	
TJ	Junction Temperature	+200	°C	
T _{STG}	Storage Temperature	- 65 to +150	°C	

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance	2.2	°C/W
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October 1992 1/3

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

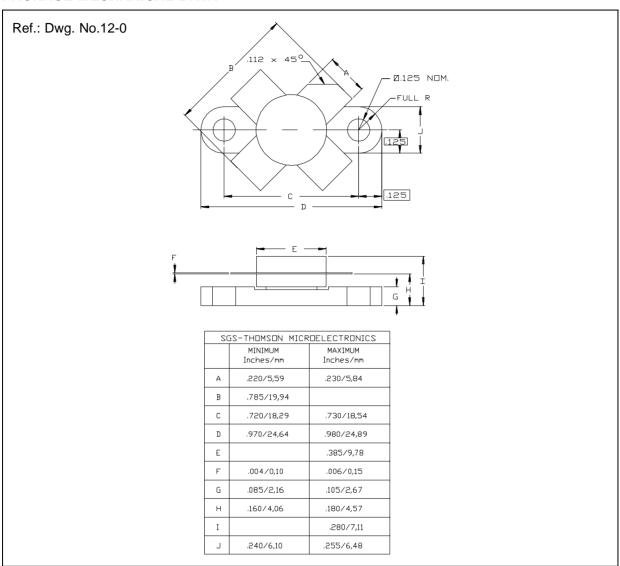
Symbol	Test Conditions	Value			Unit		
		Min.	Тур.	Max.	Oiiit		
ВУсво	I _C = 200mA	$I_E = 0mA$		65	_	_	V
BVces	I _C = 200mA	$V_{BE} = 0V$		65	_	_	V
BV _{CEO}	I _C = 200mA	$I_B = 0mA$		35	_	_	V
BV _{EBO}	I _E = 10mA	$I_C = 0mA$		4.0	_	_	V
I _{CBO}	V _{CB} = 30V	I _E = 0mA		_	_	1	mA
h _{FE}	V _{CE} = 5V	$I_C = .5A$		5	_	200	_

DYNAMIC

Symbol	Test Conditions			Value			Unit
Symbol				Min.	Тур.	Max.	Onit
Pout	f = 30 MHz	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 25 \text{ mA}$	30	_	_	W
G_P	f = 30 MHz	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 25 \text{ mA}$	18	20	_	dB
IMD	f = 30 MHz	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 25 \text{ mA}$	_	- 32	- 28	dB
Сов	f = 1 MHz	V _{CB} = 30 V		_	_	65	pF

Note: $P_{IN} = 0.48W$

PACKAGE MECHANICAL DATA



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